

### ■ Features

High Output Power: P1dB=42.0dBm(Typ.)

High Gain: G1dB=7.5dB(Typ.)

High Power Added Efficiency: PAE=32%(Typ.)

• Broad Band: Frequency=9.5 to10.5GHz

· Internally Matched

· Hermetically Sealed Package

# Description

The FLM0910-15F is a power GaAs FET that is internally matched for standard communication bands to provide optimum power and gain in a 50ohm system.



ABSOLUTE MAXIMUM RATING (Case Temperature  $T_c$ =25 deg.C)

Item	Symbol	Rating U			
Drain-Source Voltage	V <sub>DS</sub>	15	V		
Gate-Source Voltage	$V_{GS}$	-5	V		
Total Power Dissipation	P <sub>T</sub>	57.7	W		
Storage Temperature	T <sub>stg</sub>	-65 to +175	deg.C		
Channel Temperature	T <sub>ch</sub>	175	deg.C		

#### RECOMMENDED OPERATING CONDITION

Item	Symbol	Condition	Limit	Unit
Drain-Source Voltage	$V_{DS}$		<=10	V
Forward Gate Current	$I_{GF}$	Rg=50ohm	<=16.7	mA
Reverse Gate Current	$I_{GR}$	Rg=50ohm	>= -3.62	mA

ELECTRICAL CHARACTERISTICS (Case Temperature  $T_c=25 \text{ deg.C}$ )

Thomas	C	Condition		Limit		
Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Saturated Drain Current	I <sub>DSS</sub>	VDS=5V, VGS=0V	-	7.0	10.5	Α
Trans Conductance	gm	VDS=5V, IDS=3.5A	-	4500	-	mS
Pinch-off Voltage	V <sub>P</sub>	VDS=5V, IDS=300mA	-0.5	-1.5	-3.0	V
Gate-Source Breakdown Voltage	$V_{GSO}$	IGS=-300uA	-5.0	-	-	V
Output Power at 1dB G.C.P.	P <sub>1dB</sub>		41.0	42.0	-	dBm
Power Gain at 1dB G.C.P.	G <sub>1dB</sub>	VDS=10V	6.5	7.5	-	dB
Drain Current	I <sub>DSR</sub>	Ids(DC)=3.6A(typ.)	-	4.0	5.0	Α
Power Added Efficiency	PAE	f=9.5 to 10.5 GHz	-	32	-	%
Gain Flatness	ΔG		-	-	1.2	dB
Thermal Resistance	R <sub>th</sub>	Channel to Case	-	2.3	2.6	deg.C/W
Channel Temperature Rise	$\Delta T_{ch}$	(V <sub>DS</sub> x I <sub>DSR</sub> – Pout + Pin ) x R <sub>th</sub>	-	-	100	deg.C

G.C.P.: Gain Compression Point, S.C.L.: Single Carrier Level

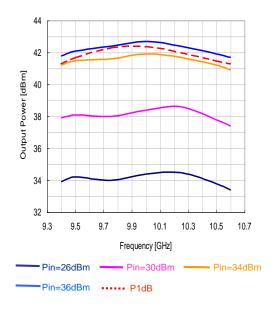
CASE STYLE	IB	
RoHS Compliance	YES	
ESD	Class 3A	4000V to < 8000V

Note: Based on ANSI/ESDA/JEDEC JS-001-2012(C=100pF, R=1.5kohm)

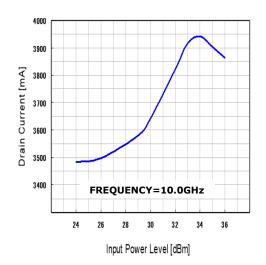


## RF Characteristics

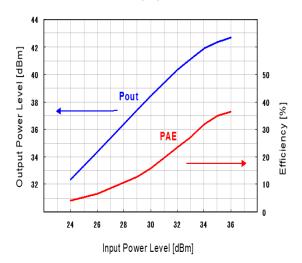
# OUTPUT POWER v.s. FREQUENCY $V_{DS}=10V$ , $I_{DS(DC)}=3600$ mA



# DRAIN CURRENT v.s. INPUT POWER $V_{DS}$ =10V, $I_{DS(DC)}$ =3600mA

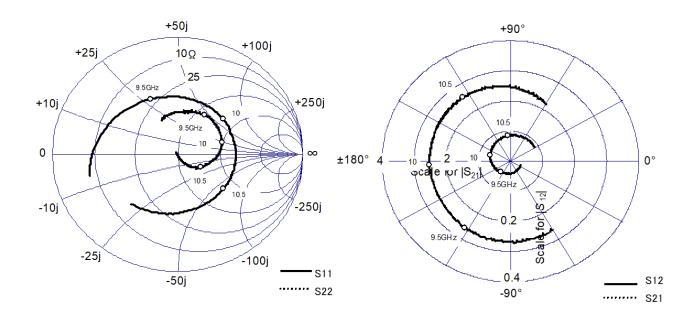


# OUTPUT POWER , POWER ADDED EFFICIENCY v.s. INPUT POWER $V_{DS}$ =10V, $I_{DS(DC)}$ =3600mA





## • S-Parameter

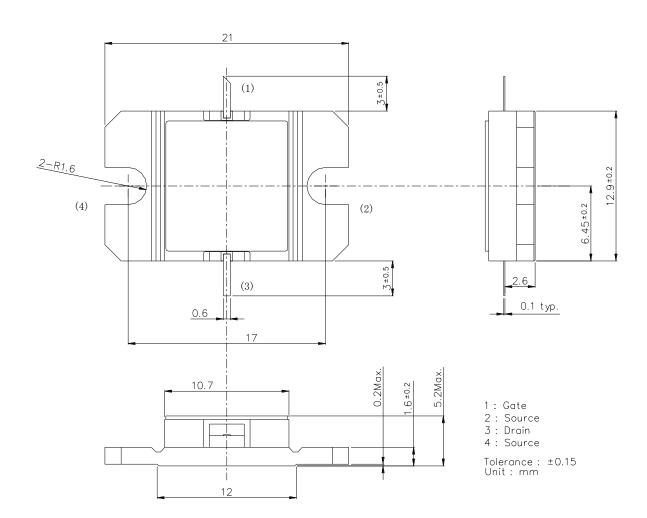


VDS=10.0V, IDS=3600mA

Freq.	<b>S1</b> 1	l	S2	1	S1:	2	S22	2
[GHz]	mag	ang	mag	ang	mag	ang	mag	ang
9.3	0.589	147.4	2.678	-98.7	0.041	-88.1	0.374	77.2
9.4	0.544	130.9	2.649	-111.1	0.043	-107.6	0.387	67.0
9.5	0.520	114.6	2.618	-122.5	0.046	-127.3	0.397	57.8
9.6	0.498	98.6	2.569	-134.0	0.049	-141.0	0.401	49.7
9.7	0.488	83.8	2.538	-144.9	0.054	-155.7	0.396	41.6
9.8	0.477	68.8	2.524	-155.2	0.059	-169.5	0.390	33.1
9.9	0.474	54.6	2.509	-165.9	0.061	177.5	0.380	24.6
10.0	0.471	39.4	2.524	-176.9	0.066	163.5	0.368	15.6
10.1	0.467	25.4	2.514	172.4	0.069	149.1	0.349	7.1
10.2	0.462	10.4	2.519	161.2	0.073	136.4	0.321	-1.2
10.3	0.463	-4.6	2.553	150.2	0.077	121.6	0.290	-10.1
10.4	0.468	<b>−21.7</b>	2.563	137.9	0.083	109.8	0.250	-20.5
10.5	0.469	-39.2	2.591	125.3	0.085	95.4	0.215	-30.7
10.6	0.478	-58.6	2.554	112.4	0.088	84.0	0.174	-40.2
10.7	0.488	<b>−77.5</b>	2.514	98.8	0.090	69.4	0.126	<b>-48.5</b>



# Package Out line Case Style : IB





# For Safety, Observe the Following Procedures Environmental Management

- Do not put this product into the mouth.
- Do not alter the form of this product into a gas, powder, or liquid through burning, crushing, or chemical processing as these by-products are dangerous to the human body if inhaled, ingested, or swallowed.
- Respect all applicable laws of the country when discarding this product.
  This product must be disposed in accordance with methods specified by applicable hazardous waste procedures.

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